# Boncheol Ku

List of Publications by Year
in descending order



| 14 | 721 | 687363 13 | 1058476 14 |
|---|---|---|---|
| papers | citations | h-index | g-index |

| 14 | 14 | 14 | 807 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Cellulose Nanocrystal Based Bioâ€Memristor as a Green Artificial Synaptic Device for Neuromorphic Computing Applications. Advanced Materials Technologies, 2022, 7, 2100744. | 5.8 | 29 |
| 2 | Improved switching and synapse characteristics using PEALD SiO2 thin film in Cu/SiO2/ZrO2/Pt device. Applied Surface Science, 2021, 547, 149140. | 6.1 | 12 |
| 3 | Analog Synaptic Transistor with Al-Doped HfO<sub>2</sub> Ferroelectric Thin Film. ACS Applied Materials & Interfaces, 2021, 13, 52743-52753. | 8.0 | 37 |
| 4 | Ar ion plasma surface modification on the heterostructured TaOx/InGaZnO thin films for flexible memristor synapse. Journal of Alloys and Compounds, 2020, 822, 153625. | 5.5 | 39 |
| 5 | The coexistence of threshold and memory switching characteristics of ALD HfO<sub>2</sub> memristor synaptic arrays for energy-efficient neuromorphic computing. Nanoscale, 2020, 12, 14120-14134. | 5.6 | 88 |
| 6 | Two-terminal artificial synapse with hybrid organicâ€“inorganic perovskite (CH3NH3)PbI3 and low operating power energy (âˆ¼47ÂfJ/Ì¼m2). Journal of Alloys and Compounds, 2020, 833, 155064. | 5.5 | 41 |
| 7 | Bio-realistic synaptic characteristics in the cone-shaped ZnO memristive device. NPG Asia Materials, 2019, 11, . | 7.9 | 55 |
| 8 | Study of in Situ Silver Migration in Amorphous Boron Nitride CBRAM Device. ACS Applied Materials & Interfaces, 2019, 11, 23329-23336. | 8.0 | 52 |
| 9 | Improved resistive switching and synaptic characteristics using Ar plasma irradiation on the Ti/HfO2 interface. Journal of Alloys and Compounds, 2019, 797, 277-283. | 5.5 | 28 |
| 10 | Compliance-Free, Digital SET and Analog RESET Synaptic Characteristics of Sub-Tantalum Oxide Based Neuromorphic Device. Scientific Reports, 2018, 8, 1228. | 3.3 | 91 |
| 11 | Interface engineering of ALD HfO2-based RRAM with Ar plasma treatment for reliable and uniform switching behaviors. Journal of Alloys and Compounds, 2018, 735, 1181-1188. | 5.5 | 85 |
| 12 | Influence of oxygen vacancies in ALD HfO2-x thin films on non-volatile resistive switching phenomena with a Ti/HfO2-x/Pt structure. Applied Surface Science, 2018, 434, 822-830. | 6.1 | 85 |
| 13 | Structural engineering of tantalum oxide based memristor and its electrical switching responses using rapid thermal annealing. Journal of Alloys and Compounds, 2018, 759, 44-51. | 5.5 | 33 |
| 14 | Engineering synaptic characteristics of TaO<sub>x</sub>/HfO<sub>2</sub> bi-layered resistive switching device. Nanotechnology, 2018, 29, 415204. | 2.6 | 46 |